1SMC5.0AT3Series

1500 Watt Peak Power Zener Transient Voltage Suppressors

Unidirectional*

The SMC series is designed to protect voltage sensitive components from high voltage, high energy transients. They have excellent clamping capability, high surge capability, low zener impedance and fast response time. The SMC series is supplied in ON Semiconductor's exclusive, cost-effective, highly reliable Surmetic[™] package and is ideally suited for use in communication systems, automotive, numerical controls, process controls, medical equipment, business machines, power supplies and many other industrial/consumer applications.

Features

- Working Peak Reverse Voltage Range 5.0 V to 78 V
- Standard Zener Breakdown Voltage Range 6.7 V to 91.25 V
- Peak Power 1500 Watts @ 1 ms
- ESD Rating of Class 3 (>16 KV) per Human Body Model
- Maximum Clamp Voltage @ Peak Pulse Current
- Low Leakage $< 5 \mu A$ Above 10 V
- UL 497B for Isolated Loop Circuit Protection
- Maximum Temperature Coefficient Specified
- Response Time is Typically < 1 ns
- Pb–Free Packages are Available

Mechanical Characteristics:

CASE: Void-free, transfer-molded, thermosetting plastic **FINISH:** All external surfaces are corrosion resistant and leads are

readily solderable

MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES: 260°C for 10 Seconds

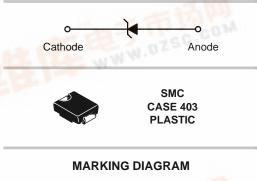
LEADS: Modified L–Bend providing more contact area to bond pads **POLARITY:** Cathode indicated by molded polarity notch **MOUNTING POSITION:** Any



ON Semiconductor®

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PLASTIC SURFACE MOUNT ZENER TRANSIENT VOLTAGE SUPPRESSORS 5.0–78 VOLTS 1500 WATT PEAK POWER





= Assembly Location

- = Year
- WW = Work Week
- Gxx = Device Code (Refer to page 3)
 - = Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
1SMCxxxAT3	SMC	2500/Tape & Reel
1SMCxxxAT3G	SMC (Pb–Free)	2500/Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Bidirectional devices will not be available in this series.

DEVICE MARKING INFORMATION

See specific marking information in the device marking column of the Electrical Characteristics table on page 3 of this data sheet.

August, 2005 – Rev. 4

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Rating	Symbol	Value	Unit
Peak Power Dissipation (Note 1) @ $T_L = 25^{\circ}C$, Pulse Width = 1 ms	P _{PK}	1500	W
DC Power Dissipation @ T _L = 75°C Measured Zero Lead Length (Note 2) Derate Above 75°C Thermal Resistance from Junction to Lead	Ρ _D R _{θJL}	4.0 54.6 18.3	W mW/°C °C/W
DC Power Dissipation (Note 3) @ T _A = 25°C Derate Above 25°C Thermal Resistance from Junction to Ambient	P _D R _{θJA}	0.75 6.1 165	W mW/°C °C/W
Forward Surge Current (Note 4) @ T _A = 25°C	I _{FSM}	200	А
Operating and Storage Temperature Range	T _J , T _{stg}	-65 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. 10 x 1000 μ s, non-repetitive. 2. 1 in square copper pad, FR-4 board.

3. FR-4 board, using ON Semiconductor minimum recommended footprint, as shown in 403 case outline dimensions spec.

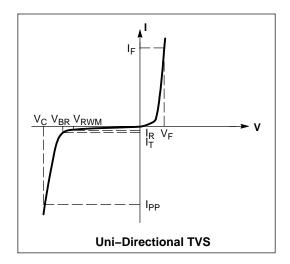
4. 1/2 sine wave (or equivalent square wave), PW = 8.3 ms, duty cycle = 4 pulses per minute maximum.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless

otherwise noted,	$V_{F} = 3.5 V$	′ Max @ I _F =	100 A) (Note 5)
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Symbol	Parameter					
I _{PP}	Maximum Reverse Peak Pulse Current					
V _C	Clamping Voltage @ IPP					
V _{RWM} Working Peak Reverse Voltage						
I _R	Maximum Reverse Leakage Current @ V _{RWM}					
V _{BR}	Breakdown Voltage @ I _T					
Ι _Τ	Test Current					
١ _F	Forward Current					
V _F	Forward Voltage @ I _F					

5. 1/2 sine wave or equivalent, PW = 8.3 ms non-repetitive duty cycle



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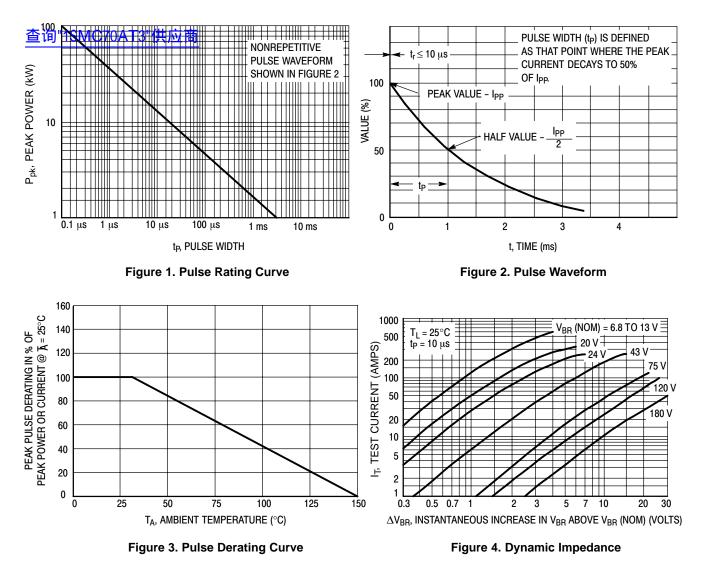
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

		V		Breakdown Voltage			V _C @ I _{PP} (Note 8)		
	Davias	V _{RWM} (Note 6)	I _R @ V _{RWM}	V _{BR} Volts (Note 7)			@ I _T	Vc	I _{PP}
Device*	Device Marking	Volts	μA	Min	Nom	Мах	mA	Volts	Amps
1SMC5.0AT3, G	GDE	5.0	1000	6.4	6.7	7.0	10	9.2	163
1SMC6.0AT3, G	GDG	6.0	1000	6.67	7.02	7.37	10	10.3	145.6
1SMC6.5AT3, G	GDK	6.5	500	7.22	7.6	7.98	10	11.2	133.9
1SMC7.0AT3, G	GDM	7.0	200	7.78	8.19	8.6	10	12	125
1SMC7.5AT3, G	GDP	7.5	100	8.33	8.77	9.21	1	12.9	116.3
1SMC8.0AT3, G	GDR	8.0	50	8.89	9.36	9.83	1	13.6	110.3
1SMC8.5AT3, G	GDT	8.5	25	9.44	9.92	10.4	1	14.4	104.2
1SMC9.0AT3, G	GDV	9.0	10	10	10.55	11.1	1	15.4	97.4
1SMC10AT3, G	GDX	10	5	11.1	11.7	12.3	1	17	88.2
1SMC12AT3, G	GEE	12	5	13.3	14	14.7	1	19.9	75.3
1SMC13AT3, G	GEG	13	5	14.4	15.15	15.9	1	21.5	69.7
1SMC14AT3, G 1SMC15AT3, G 1SMC16AT3, G 1SMC17AT3, G	GEK GEM GEP GER	14 15 16 17	5 5 5 5	15.6 16.7 17.8 18.9	16.4 17.6 18.75 19.9	17.2 18.5 19.7 20.9	1 1 1	23.2 24.4 26 27.6	64.7 61.5 57.7 53.3
1SMC18AT3, G 1SMC20AT3, G 1SMC22AT3, G 1SMC24AT3, G	GET GEV GEX GEZ	18 20 22 24	5 5 5 5	20 22.2 24.4 26.7	21.05 23.35 25.65 28.1	22.1 24.5 26.9 29.5	1 1 1	29.2 32.4 35.5 38.9	51.4 46.3 42.2 38.6
1SMC26AT3, G	GFE	26	5	28.9	30.4	31.9	1	42.1	35.6
1SMC28AT3, G	GFG	28	5	31.1	32.75	34.4	1	45.4	33
1SMC30AT3, G	GFK	30	5	33.3	35.05	36.8	1	48.4	31
1SMC33AT3, G	GFM	33	5	36.7	38.65	40.6	1	53.3	28.1
1SMC36AT3, G	GFP	36	5	40	42.1	44.2	1	58.1	25.8
1SMC40AT3, G	GFR	40	5	44.4	46.75	49.1	1	64.5	32.2
1SMC43AT3, G	GFT	43	5	47.8	50.3	52.8	1	69.4	21.6
1SMC45AT3	GFV	45	5	50	52.65	55.3	1	72.2	20.6
1SMC48AT3, G	GFX	48	5	53.3	56.1	58.9	1	77.4	19.4
1SMC51AT3, G	GFZ	51	5	56.7	59.7	62.7	1	82.4	18.2
1SMC54AT3, G	GGE	54	5	60	63.15	66.3	1	87.1	17.2
1SMC58AT3, G	GGG	58	5	64.4	67.8	71.2	1	93.6	16
1SMC60AT3 1SMC64AT3, G 1SMC70AT3, G 1SMC75AT3, G 1SMC78AT3, G	GGK GGM GGP GGR GGT	60 64 70 75 78	5 5 5 5 5 5	66.7 71.1 77.8 83.3 86.7	70.2 74.85 81.9 87.7 91.25	73.7 78.6 86 92.1 95.8	1 1 1 1	96.8 103 113 121 126	15.5 14.6 13.3 12.4 11.4

6. A transient suppressor is normally selected according to the maximum working peak reverse voltage (V_{RWM}), which should be equal to or greater than the DC or continuous peak operating voltage level.
7. V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C.
8. Surge current waveform per Figure 2 and derate per Figure 3 of the General Data – 1500 Watt at the beginning of this group.

*The "G" suffix indicates Pb-Free package available.

1SMC5.0AT3 Series



UL RECOGNITION

The entire series has *Underwriters Laboratory Recognition* for the classification of protectors (QVGV2) under the UL standard for safety 497B and File #116110. Many competitors only have one or two devices recognized or have recognition in a non-protective category. Some competitors have no recognition at all. With the UL497B recognition, our parts successfully passed several tests including Strike Voltage Breakdown test, Endurance Conditioning, Temperature test, Dielectric Voltage-Withstand test, Discharge test and several more.

Whereas, some competitors have only passed a flammability test for the package material, we have been recognized for much more to be included in their Protector category.

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APPLICATION NOTES

RESPONSE TIME

In most applications, the transient suppressor device is placed in parallel with the equipment or component to be protected. In this situation, there is a time delay associated with the capacitance of the device and an overshoot condition associated with the inductance of the device and the inductance of the connection method. The capacitive effect is of minor importance in the parallel protection scheme because it only produces a time delay in the transition from the operating voltage to the clamp voltage as shown in Figure 5.

The inductive effects in the device are due to actual turn-on time (time required for the device to go from zero current to full current) and lead inductance. This inductive effect produces an overshoot in the voltage across the equipment or component being protected as shown in Figure 6. Minimizing this overshoot is very important in the application, since the main purpose for adding a transient suppressor is to clamp voltage spikes. The SMC series have a very good response time, typically < 1 ns and negligible inductance. However, external inductive effects could produce unacceptable overshoot. Proper circuit layout,

minimum lead lengths and placing the suppressor device as close as possible to the equipment or components to be protected will minimize this overshoot.

Some input impedance represented by Z_{in} is essential to prevent overstress of the protection device. This impedance should be as high as possible, without restricting the circuit operation.

DUTY CYCLE DERATING

The data of Figure 1 applies for non-repetitive conditions and at a lead temperature of 25°C. If the duty cycle increases, the peak power must be reduced as indicated by the curves of Figure 7. Average power must be derated as the lead or ambient temperature rises above 25°C. The average power derating curve normally given on data sheets may be normalized and used for this purpose.

At first glance the derating curves of Figure 7 appear to be in error as the 10 ms pulse has a higher derating factor than the 10 μ s pulse. However, when the derating factor for a given pulse of Figure 7 is multiplied by the peak power value of Figure 1 for the same pulse, the results follow the expected trend.

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TYPICAL PROTECTION CIRCUIT

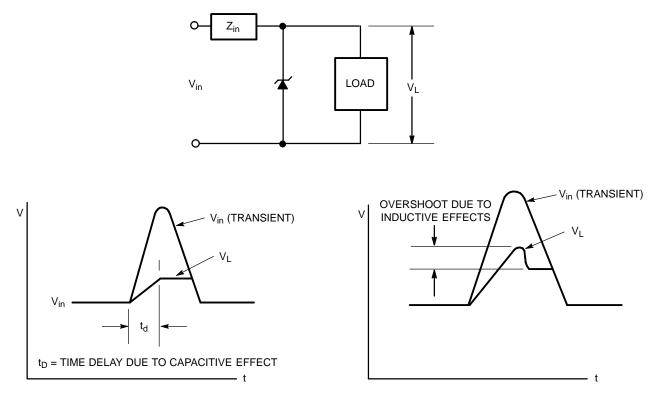
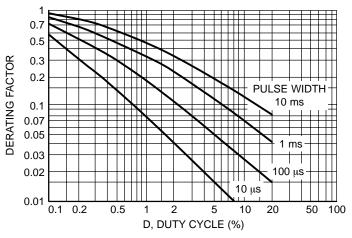


Figure 5.



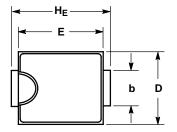


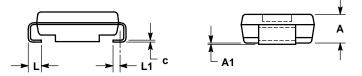


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PACKAGE DIMENSIONS

SMC CASE 403–03 ISSUE E





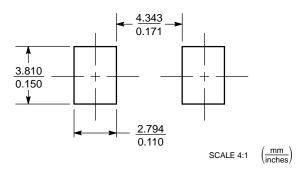
NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: INCH. 3. D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P.

3. D DIMENSION SHALL BE MEASURED WITHIN DIMENSION I 4. 403-01 THRU -02 OBSOLETE, NEW STANDARD 403-03.

	м	ILLIMETE	RS	INCHES			
DIM	MIN	NOM	MAX	MIN	MAX		
Α	1.90	2.13	2.41	0.075	0.084	0.095	
A1	0.05	0.10	0.15	0.002	0.004	0.006	
b	2.92	3.00	3.07	0.115	0.118	0.121	
С	0.15	0.23	0.30	0.006	0.009	0.012	
D	5.59	5.84	6.10	0.220	0.230	0.240	
E	6.60	6.86	7.11	0.260	0.270	0.280	
HE	7.75	7.94	8.13	0.305	0.313	0.320	
L	0.76	1.02	1.27	0.030	0.040	0.050	
L1	0.51 REF				0.020 REF		

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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